

APR 23 2004  
**OFFICIAL**

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the application of: Anthony *et al.*

Docket: TI-24953

Serial No.: 09/116,138

Examiner: W. D. Coleman

Filed: 07/15/98

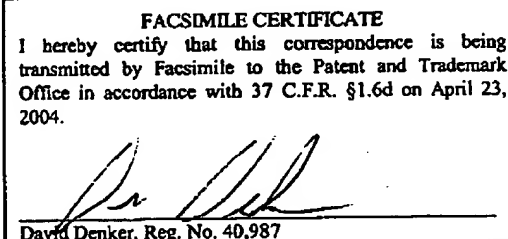
Art Unit: 2823

For: High Permittivity Silicate Gate Dielectric

**REPLY PURSUANT TO 37 C.F.R. § 1.111**

April 14, 2004

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450



Examiner:

In response to the Office Action dated December 16, 2003, please amend the above-identified patent application as follows:

**IN THE CLAIMS**

A. Please rejoin claims 28, 29, 46, 71, 72, and 73.

B. Please replace the claims with the claims on the following sheets.

Claims 1 and 46 are amended below.

Withdrawn claims 2 - 25, 36 - 40, 47 - 70, and 74 - 80 are canceled below.

Claims 31 - 35 and 41 - 45 were canceled in a previous amendment.

With the rejoinder requested above, this leaves claims 1, 26 - 30, 46, and 71 - 73 active.

1. (Currently amended) A method of fabricating a field-effect transistor device on an integrated circuit, comprising the steps of:  
providing a single-crystal silicon substrate;  
forming a metal silicate dielectric layer on the substrate; and  
forming a conductive transistor gate overlying the metal silicate dielectric layer.